

isc Silicon NPN Power Transistor

2SC2665

DESCRIPTION

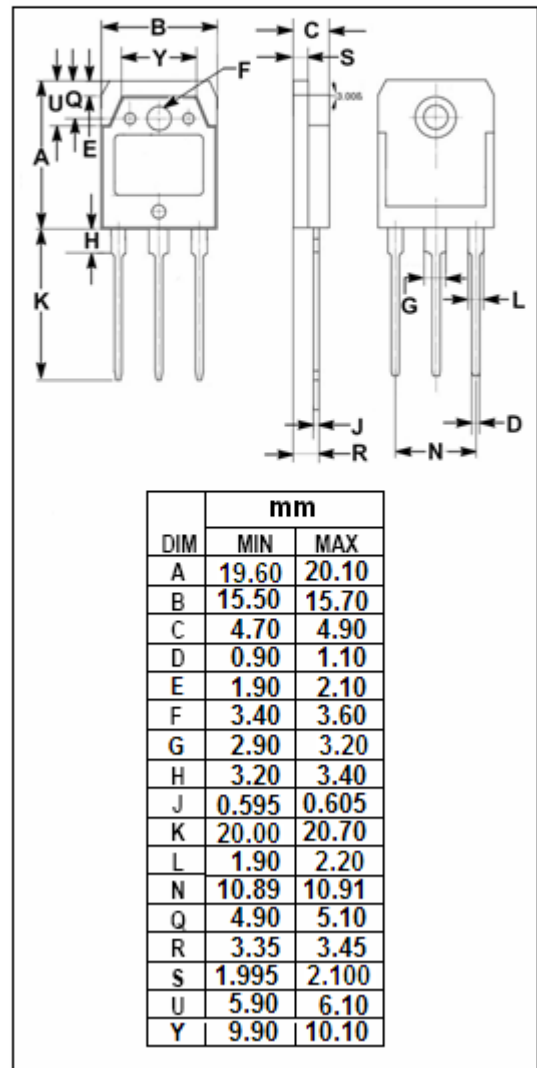
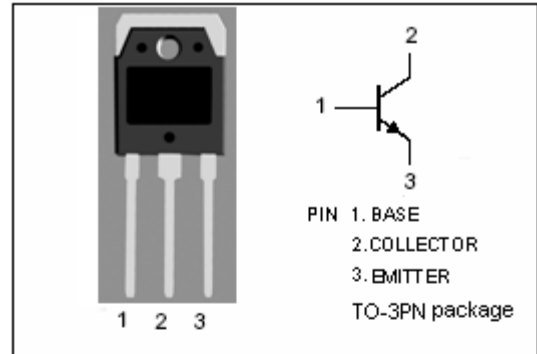
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 80V(\text{Min})$
- Wide Area of Safe Operation

APPLICATIONS

- Designed for audio frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	100	V
$V_{CEO}$	Collector-Emitter Voltage	80	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	4	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	55	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-40~150	$^\circ\text{C}$



**isc Silicon NPN Power Transistor****2SC2665****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}$ ; $R_{BE}=\infty$	80			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}$ ; $I_E=0$	100			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}$ ; $I_C=0$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}$ ; $I_B=0.3\text{A}$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=100\text{V}$ ; $I_E=0$			100	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=4\text{V}$ ; $I_C=0$			100	$\mu\text{A}$
$h_{FE-1}$	DC Current Gain	$I_C=1\text{A}$ ; $V_{CE}=4\text{V}$	40			
$h_{FE-2}$	DC Current Gain	$I_C=4\text{A}$ ; $V_{CE}=4\text{V}$	20			
$f_T$	Current-Gain—Bandwidth Product	$I_C=1\text{A}$ ; $V_{CE}=5\text{V}$		10		MHz